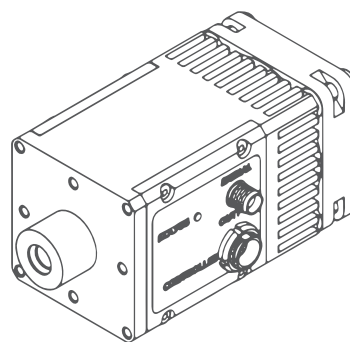


# LabM-I-10.6

## Programmable IR detection module based on HgCdTe TE cooled optically immersed photovoltaic multi-junction detector



### FEATURES

- Spectral range: 2.0 to 12.0  $\mu\text{m}$
- Frequency bandwidth: DC to 120 MHz (typ.)
- High performance and reliability
- DC offset compensation
- Built-in fan
- M4 mounting hole
- Compatible with optical accessories
- Versatility and flexibility
- Quantity discounted price
- Fast delivery
- No minimum order quantity required

### APPLICATIONS

- Gas detection, monitoring and analysis:  $\text{SO}_2$ ,  $\text{NH}_3$ ,  $\text{SF}_6$
- CBRN threats detection
- $\text{CO}_2$  laser measurements: power monitoring and control, beam profiling and positioning, calibration
- Free-space optical communication
- FTIR spectroscopy
- Medical bacteria identification
- Dentistry
- Glucose sensing
- Research and prototyping

### PROGRAMMABLE PARAMETERS

- Gain: in the 40 dB range
- Bandwidth: 1.5 MHz/15 MHz/120 MHz (typ.)
- Coupling: AC/DC
- Detector's temperature
- Output voltage offset

### INCLUDED ACCESSORIES

- 1 pc of SMA-BNC cable
- 1 pc of LEMO-DB9 cable

### DEDICATED ACCESSORIES

- PTCC-01 series TEC controller: obligatory (p. 145)
- Smart Manager software: freeware
- OTA optical threaded adapter (p. 155)
- DRB-2 base mounting system (p. 152)

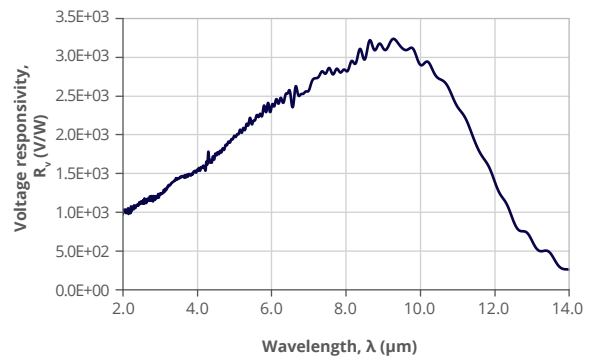
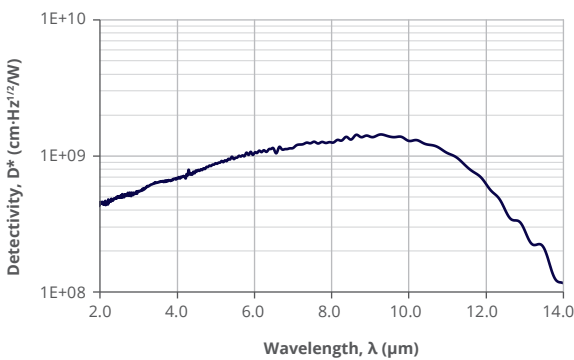
### DETECTION MODULE CONFIGURATION

| Detection module symbol                            | LabM-I-10.6  |
|--|--|
| Detector symbol                                    | PVMI-4TE-10.6-1x1-TO8-wZnSeAR-36 (p. 66)                       |
| Detector type                                      | photovoltaic, multi-junction                                   |
| Active element material                            | epitaxial HgCdTe heterostructure                               |
| Optical area, $A_o$                                | 1 mm $\times$ 1 mm   |
| Immersion  | hyperhemisphere  |
| Cooling  | 4TE  |
| Acceptance angle, $\Phi$                           | ~36 deg.   |
| Window   | wZnSeAR (3 deg. wedged zinc selenide, anti-reflection coating) |
| Preamplifier symbol                                | PIP (p. 129)   |
| Preamplifier type                                  | transimpedance, programmable                                   |
| Signal output socket                               | SMA  |
| Power supply, TE cooler, thermistor and fan socket | LEMO ECG.0B.309.CLN  |

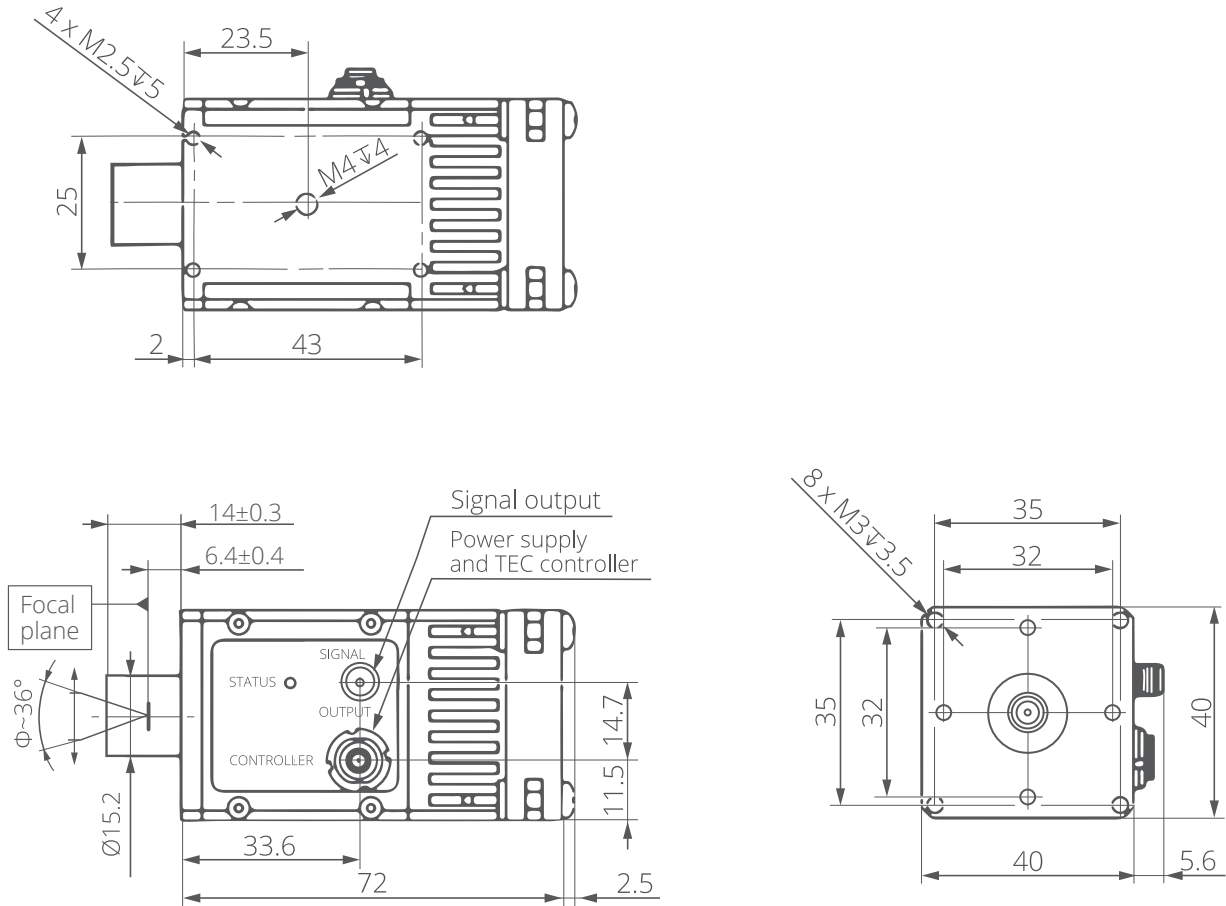
SPECIFICATION ( $T_{amb} = 293\text{ K}$ ,  $R_{load} = 50\ \Omega$ , unless otherwise noted; default module settings)

| Parameter   | Test conditions/remarks                             | Value             |                   |          | Unit   |
|---|---|-------------------|-------------------|----------|--|
|   |   | Min.              | Typ.              | Max.     |  |
| Active element temperature, $T_{chip}$                  |   | -                 | 200               | -        | K  |
| Cut-on wavelength, $\lambda_{cut-on}$ (10%)             | At 10% of peak responsivity                         | -                 | 2.0               | -        | $\mu\text{m}$                                |
| Peak wavelength, $\lambda_{peak}$                       |   | 8.0               | 9.0               | 10.0     | $\mu\text{m}$                                |
| Specific wavelength, $\lambda_{spec}$                   |   | -                 | 10.6              | -        | $\mu\text{m}$                                |
| Cut-off wavelength, $\lambda_{cut-off}$ (10%)           | At 10% of peak responsivity                         | -                 | 12.0              | -        | $\mu\text{m}$                                |
| Detectivity, $D^*$                                      | At $\lambda = \lambda_{peak}$ , $f = 10\text{ MHz}$ | -                 | $1.4 \times 10^9$ | -        | $\text{cm} \cdot \text{Hz}^{1/2} / \text{W}$ |
|   | At $\lambda = \lambda_{spec}$ , $f = 10\text{ MHz}$ | $6.0 \times 10^8$ | $1.2 \times 10^9$ | -        | $\text{cm} \cdot \text{Hz}^{1/2} / \text{W}$ |
| Output noise voltage density, $v_n$                     | At $f = 10\text{ MHz}$                              | -                 | -                 | 400      | $\text{nV} / \text{Hz}^{1/2}$                |
| Voltage responsivity, $R_v$                             | At $\lambda = \lambda_{peak}$                       | -                 | $3.2 \times 10^3$ | -        | $\text{V} / \text{W}$                        |
|   | At $\lambda = \lambda_{spec}$                       | $1.8 \times 10^3$ | $2.7 \times 10^3$ | -        | $\text{V} / \text{W}$                        |
| Low cut-off frequency, $f_{lo-DC}$                      | DC coupling selected                                | -                 | 0                 | -        | Hz   |
| Low cut-off frequency, $f_{lo-AC}$                      | AC coupling selected                                | -                 | 10                | -        | Hz   |
| High cut-off frequency, $f_{hi-H}$                      | High bandwidth selected                             | 80                | 120               | -        | MHz  |
| High cut-off frequency, $f_{hi-M}$                      | Mid bandwidth selected                              | -                 | 15                | -        | MHz  |
| High cut-off frequency, $f_{hi-L}$                      | Low bandwidth selected                              | -                 | 1.5               | -        | MHz  |
| Output impedance, $R_{out}$                             |   | -                 | 50                | -        | $\Omega$                                     |
| Output voltage swing, $V_{out}$                         |   | -                 | -                 | $\pm 1$  | V  |
| Output voltage offset, $V_{off}$                        |   | -                 | -                 | $\pm 20$ | mV   |
| Power supply voltage (positive), $+V_{sup}$             |   | -                 | +9                | -        | V  |
| Power supply voltage (negative), $-V_{sup}$             |   | -                 | -9                | -        | V  |
| Power supply current consumption (positive), $+I_{sup}$ |   | -                 | -                 | +100     | mA   |
| Power supply current consumption (negative), $-I_{sup}$ |   | -                 | -                 | -100     | mA   |
| Fan power consumption, $P_{fan}$                        |   | -                 | -                 | 900      | mW   |
| TEC voltage, $V_{TEC}$                                  |   | -                 | -                 | 8.3      | V  |
| TEC current, $I_{TEC}$                                  |   | -                 | -                 | 0.4      | A  |
| Weight  |   | -                 | 180               | -        | g  |

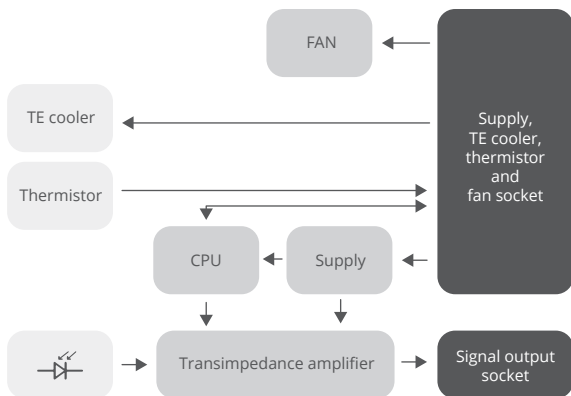
SPECTRAL RESPONSE (Typ.,  $T_{amb} = 293\text{ K}$ ,  $T_{chip} = 200\text{ K}$ )



## MECHANICAL LAYOUT (Unit: mm)



## SCHEMATIC DIAGRAM



## ABSOLUTE MAXIMUM RATINGS

| Parameter                                | Test conditions/remarks                                   | Value     | Unit               |
|--|---|-----------|--------------------|
| Ambient operating temperature, $T_{amb}$ |   | 10 to 30  | °C                 |
| Storage temperature, $T_{stg}$           |   | -20 to 50 | °C                 |
| Humidity                                 | No dew condensation                                       | 10 to 90  | %                  |
| Maximum incident optical power density   | Continuous wave (CW) or single pulses >1 $\mu$ s duration | 2.5       | W/cm <sup>2</sup>  |
|  | Single pulses <1 $\mu$ s duration                         | 10        | kW/cm <sup>2</sup> |

Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. Constant or repeated exposure to absolute maximum rating conditions may affect the quality and reliability of the device.